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THE UNITED STATES PATENT AND TRADEMARK OFFICE

TECHNOLOGY CENTER 2826

JUL 19 2002

RECEIVED

First Named
Inventor : Baowei KANG et al.
Appln. No. : 10/017,734
Filed : December 7, 2001
Title : POWER SEMICONDUCTOR SWITCHING
DEVICES WITH LOW POWER LOSS AND
METHOD FOR FABRICATING THE
SAME
Docket No. : B784.312-1

Group Art Unit: 2826
Examiner: M. L. Tran

AMENDMENT

Box Non-Fee Amendment
Assistant Commissioner for Patents
Washington, D.C. 20231

SENT VIA EXPRESS MAIL

Express Mail No.: EV 030212967 US

Sir:

This is in response to the Office Action mailed on June 14, 2002. Please amend the above-identified application as follows:

IN THE CLAIMS

Please amend claims 2-5 (marked up version attached in Appendix), such that pending claims 1-7 are as follows:

1. A low-power-loss power semiconductor switching device comprising an n-type base, a backside p⁺ emitter and general frontside structure including a cathode and a gate, wherein said switching device includes a combination of an ultra thin and lightly-doped backside p⁺ emitter formed by ion implanting and a nonuniformly doped n-type base which contains a residual layer of a priorly-diffused n⁺ layer on one side of the device.

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